



# THE DATASHEET OF STB150N3LH6





# STB150N3LH6

N-channel 30 V, 2.4 mΩ typ., 80 A, STripFET™ VI DeepGATE™ Power MOSFET in D<sup>2</sup>PAK package

Datasheet — production data

## Features

Order code	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub> <sup>(1)</sup>	P <sub>TOT</sub>
STB150N3LH6	30 V	3.0 mΩ	80 A	110 W

1. Current limited by package.

- 100% avalanche tested
- Logic level drive

## Applications

- Switching applications

## Description

This device is an N-channel Power MOSFET developed using the 6<sup>th</sup> generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R<sub>DS(on)</sub> in all packages.

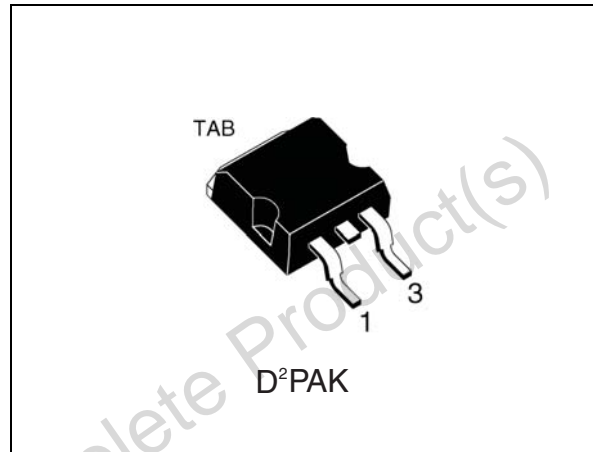


Figure 1. Internal schematic diagram

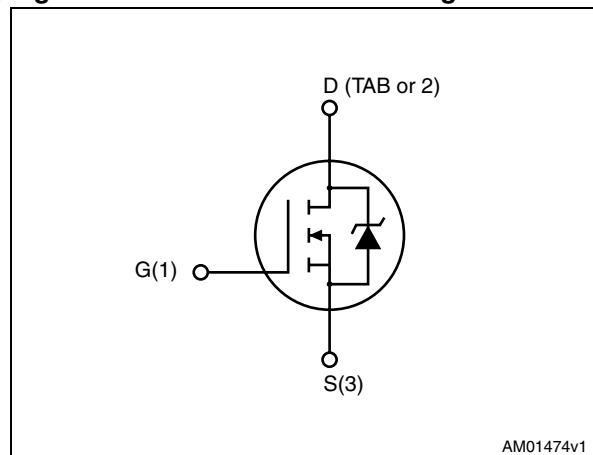


Table 1. Device summary

Order code	Marking	Package	Packaging
STB150N3LH6	150N3LH6	D <sup>2</sup> PAK	Tape and reel

# Contents

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Obsolete Product(s) - Obsolete Product(s)

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	80	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
$T_{stg}$	Storage temperature	-55 to 175	$^\circ\text{C}$
$T_j$	Operating junction temperature		$^\circ\text{C}$

- Limited by wire bonding.
- Pulse width limited by safe operating area.

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.36	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	35	$^\circ\text{C/W}$

- When mounted on 1 inch<sup>2</sup> oz Cu board.

**Table 4. Thermal resistance**

Symbol	Parameter	Value	Unit
$I_{AV}$	Not-repetitive avalanche current	40	A
$E_{AS}^{(1)}$	Single pulse avalanche energy	525	mJ

- Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = 40\text{ A}$ ,  $V_{DD} = 25\text{ V}$

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified).

**Table 5. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ( $V_{GS} = 0$ )	$I_D = 250\ \mu\text{A}$	30			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 30\text{ V}$ $V_{DS} = 30\text{ V}, T_c = 125\text{ °C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 40\text{ A}$		2.4	3.0	m $\Omega$
		$V_{GS} = 5\text{ V}, I_D = 40\text{ A}$		3.2	4.0	m $\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	3800	-	pF
$C_{oss}$	Output capacitance			725		pF
$C_{rss}$	Reverse transfer capacitance			420		pF
$Q_g$	Total gate charge	$V_{DD} = 15\text{ V}, I_D = 80\text{ A}$	-	80	-	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 10\text{ V}$		15		nC
$Q_{gd}$	Gate-drain charge	(see Figure 14)		15		nC
$R_G$	Gate input resistance	$f = 1\text{ MHz}$ gate bias bias = 0 test signal level = 20 mV open drain	-	1.5	-	$\Omega$

**Table 7. Switching on/off (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 15\text{ V}, I_D = 40\text{ A},$ $R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$ (see Figure 15)	-	15	-	ns
$t_r$	Rise time			85		ns
$t_{d(off)}$	Turn-off delay time	$V_{DD} = 15\text{ V}, I_D = 40\text{ A},$ $R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$ (see Figure 15)	-	100	-	ns
$t_f$	Fall time			40		ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40\text{ A}$ , $V_{GS} = 0$	-		1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 80\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 24\text{ V}$ (see Figure 17)	-	35		ns
$Q_{rr}$	Reverse recovery charge			26.5		nC
$I_{RRM}$	Reverse recovery current			1.7		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

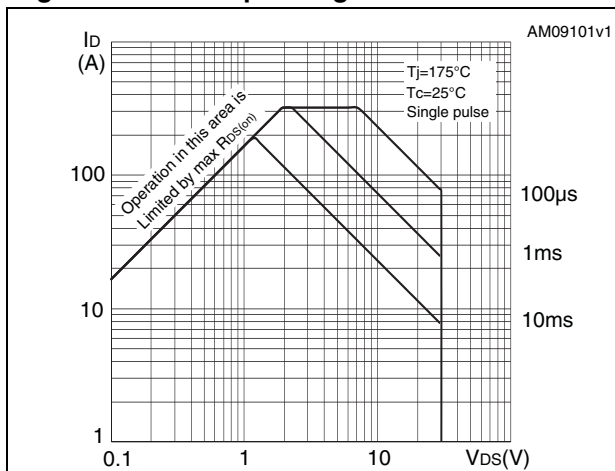


Figure 3. Thermal impedance

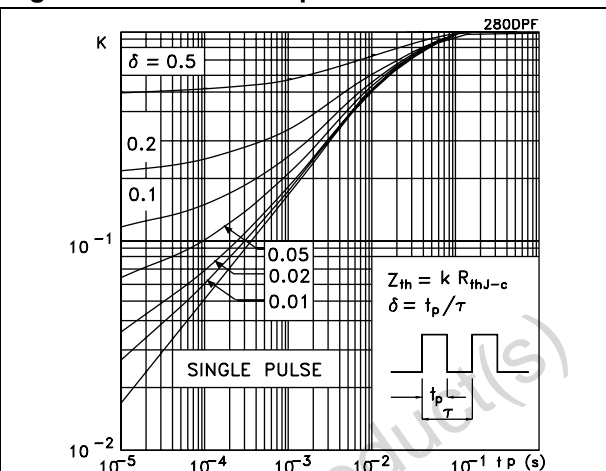


Figure 4. Output characteristics

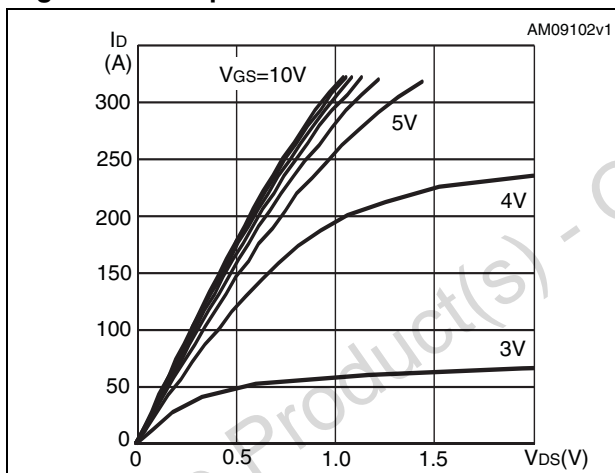


Figure 5. Transfer characteristics

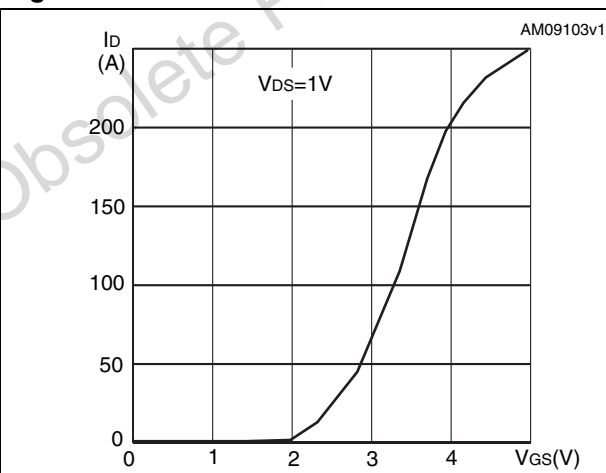


Figure 6. Normalized BV<sub>DSS</sub> vs temperature

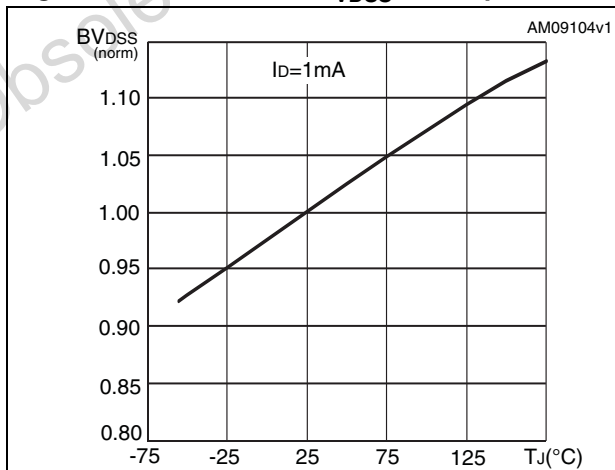


Figure 7. Static drain-source on-resistance

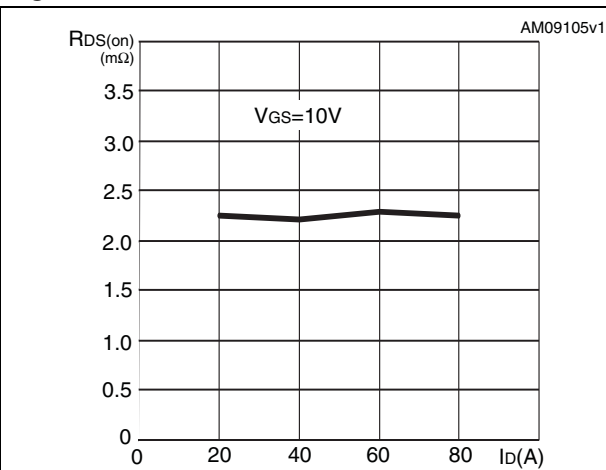


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

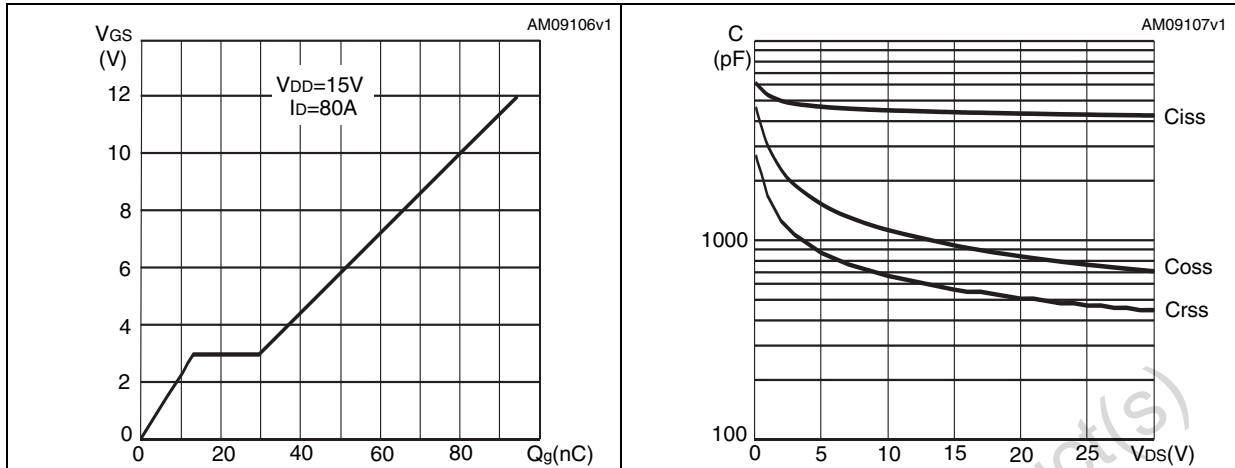


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on-resistance vs temperature

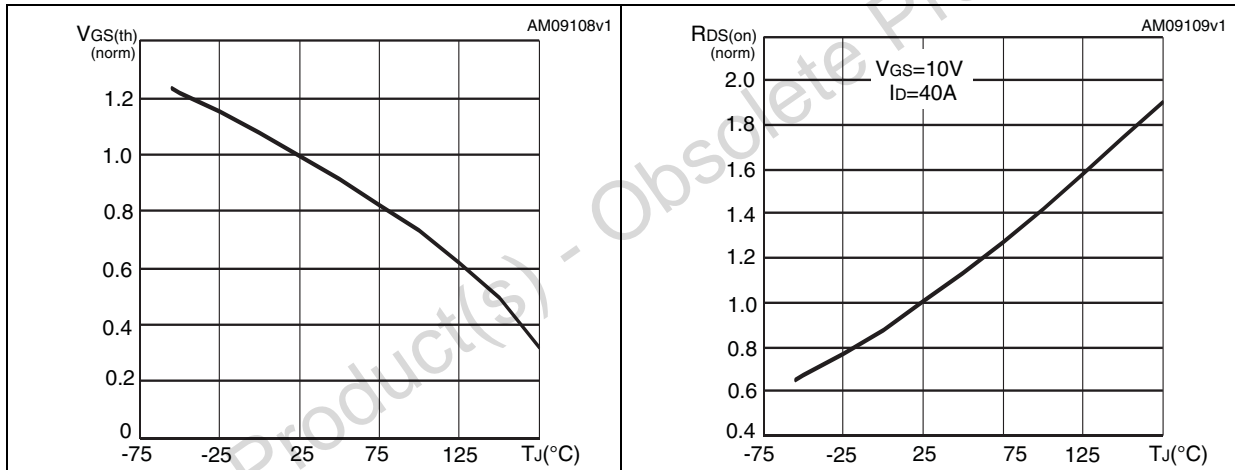
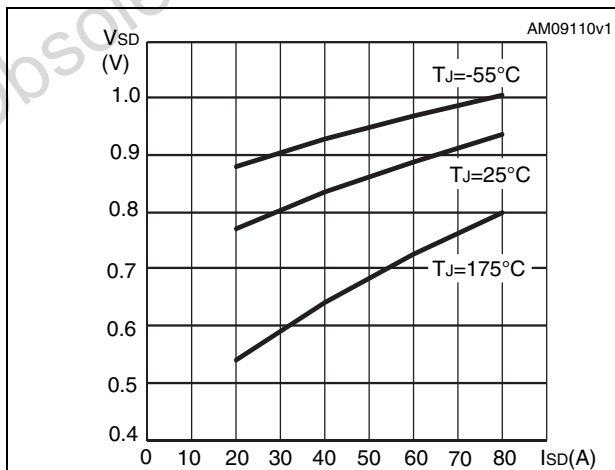
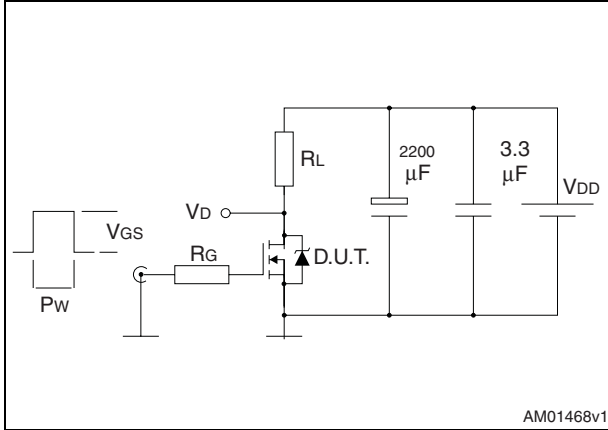


Figure 12. Source-drain diode forward characteristics



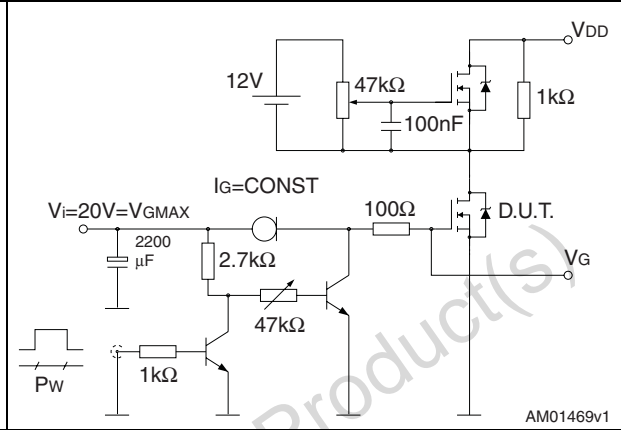
### 3 Test circuits

**Figure 13. Switching times test circuit for resistive load**



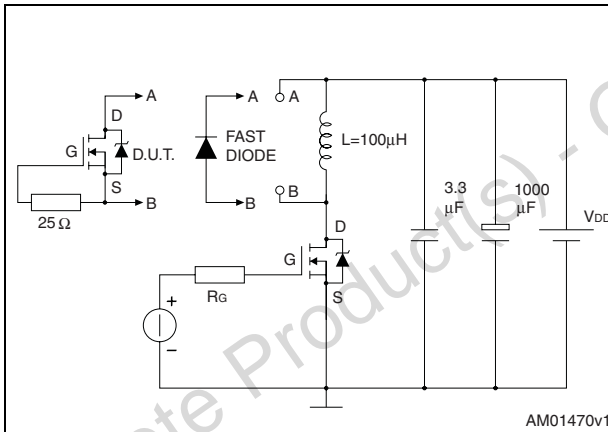
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**Figure 14. Gate charge test circuit**



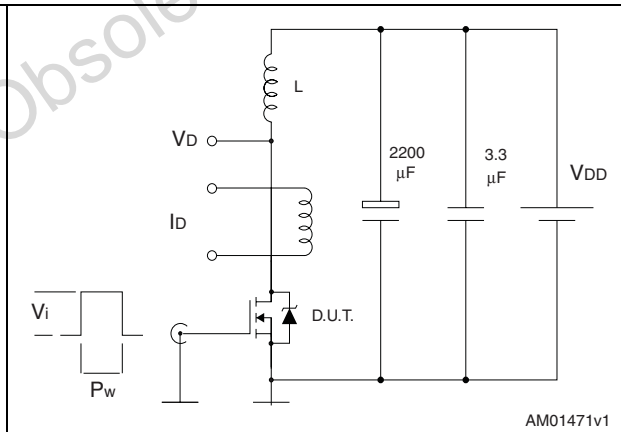
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**Figure 15. Test circuit for inductive load switching and diode recovery times**



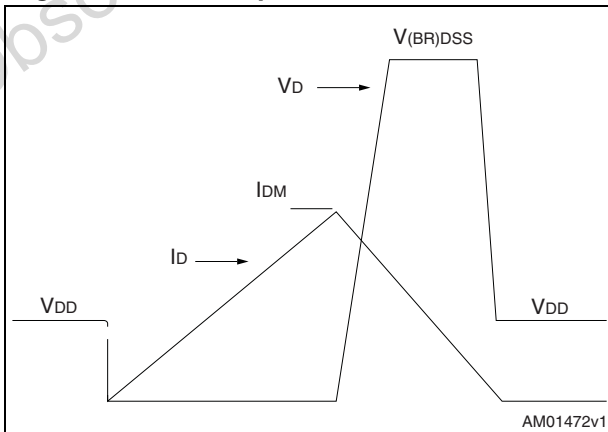
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**Figure 16. Unclamped Inductive load test circuit**



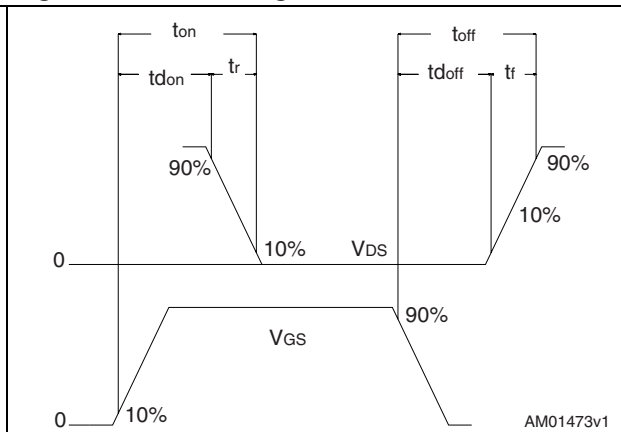
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**Figure 17. Unclamped inductive waveform**



AM01472v1

**Figure 18. Switching time waveform**



AM01473v1

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

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Table 9. D<sup>2</sup>PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 19. D<sup>2</sup>PAK (TO-263) drawing

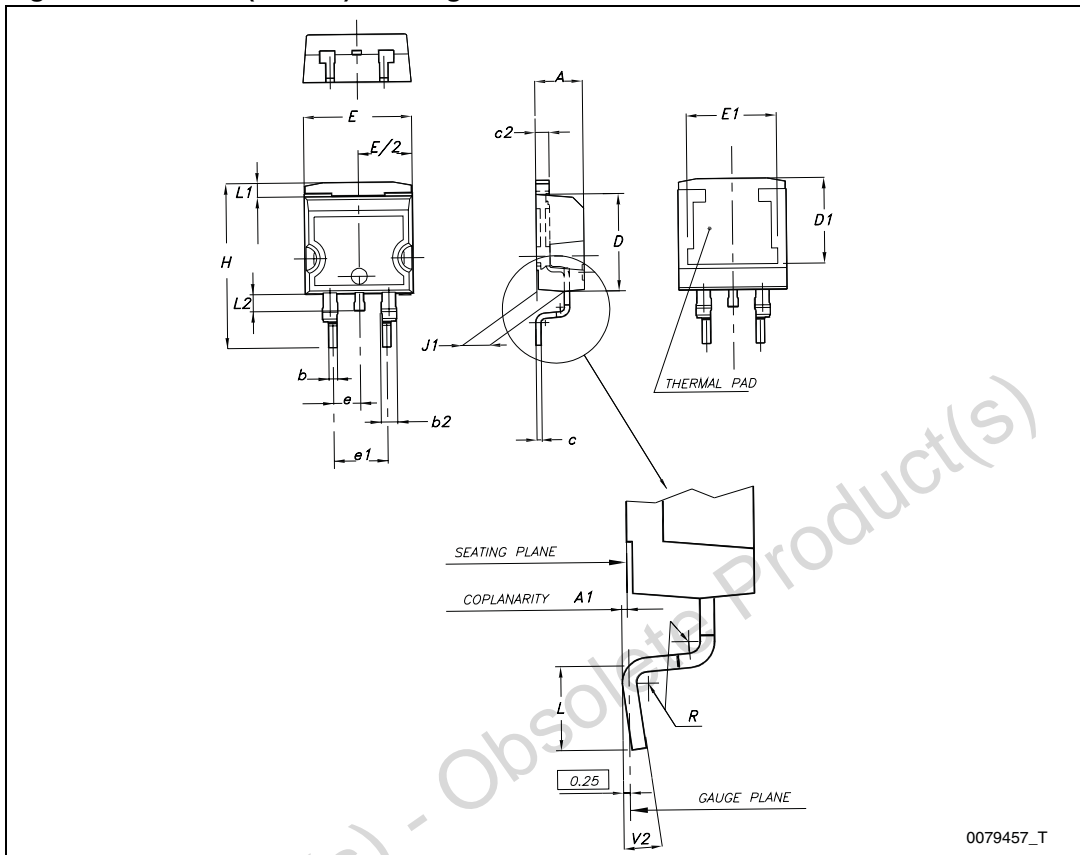
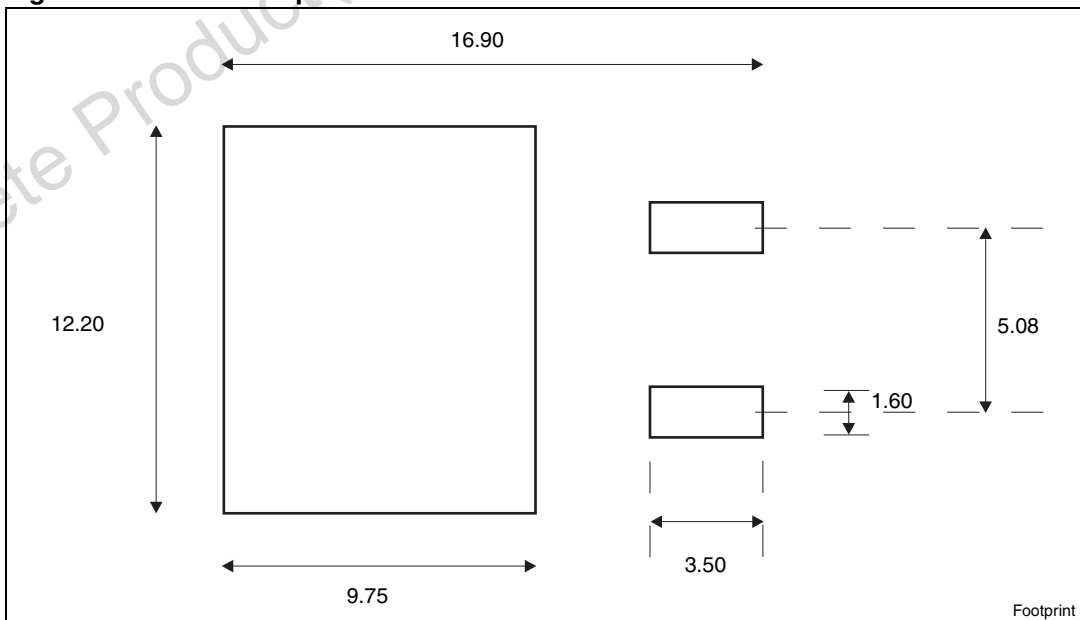


Figure 20. D<sup>2</sup>PAK footprint<sup>(a)</sup>



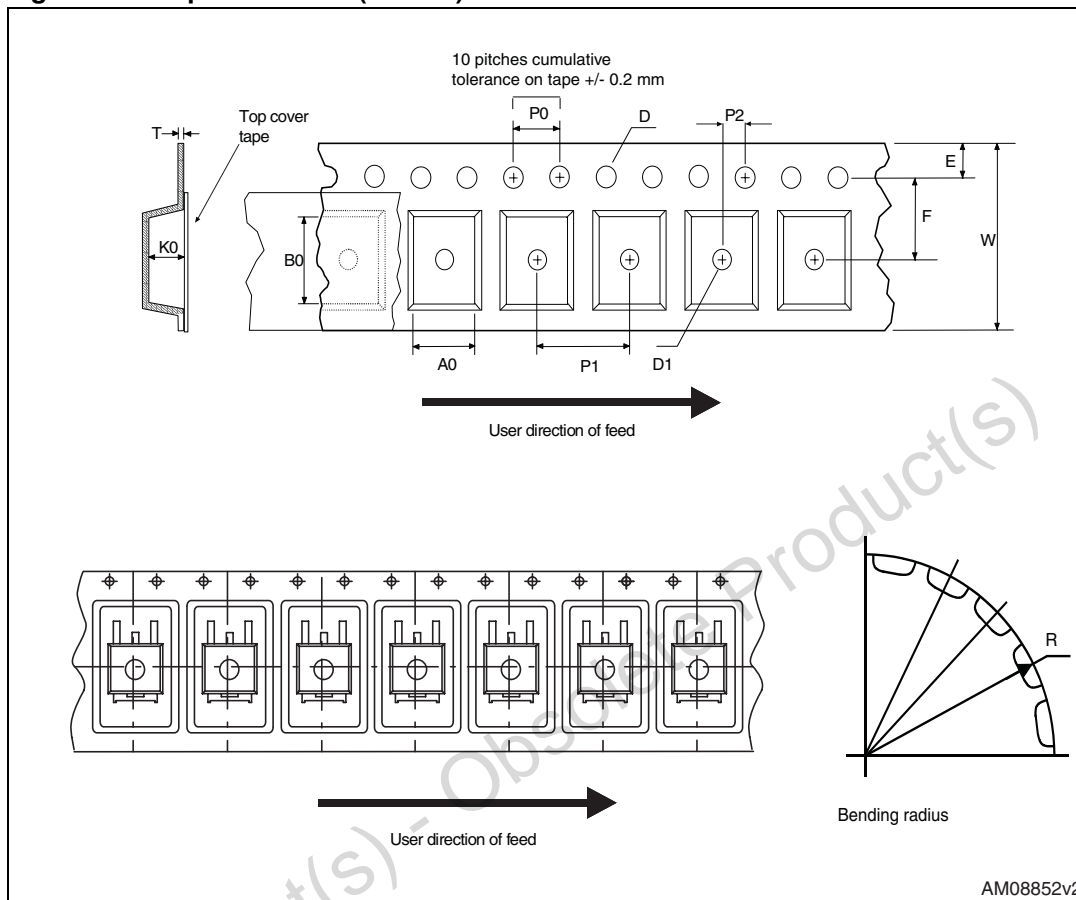
a. All dimensions are in millimeters

## 5 Packaging mechanical data

Table 10. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data

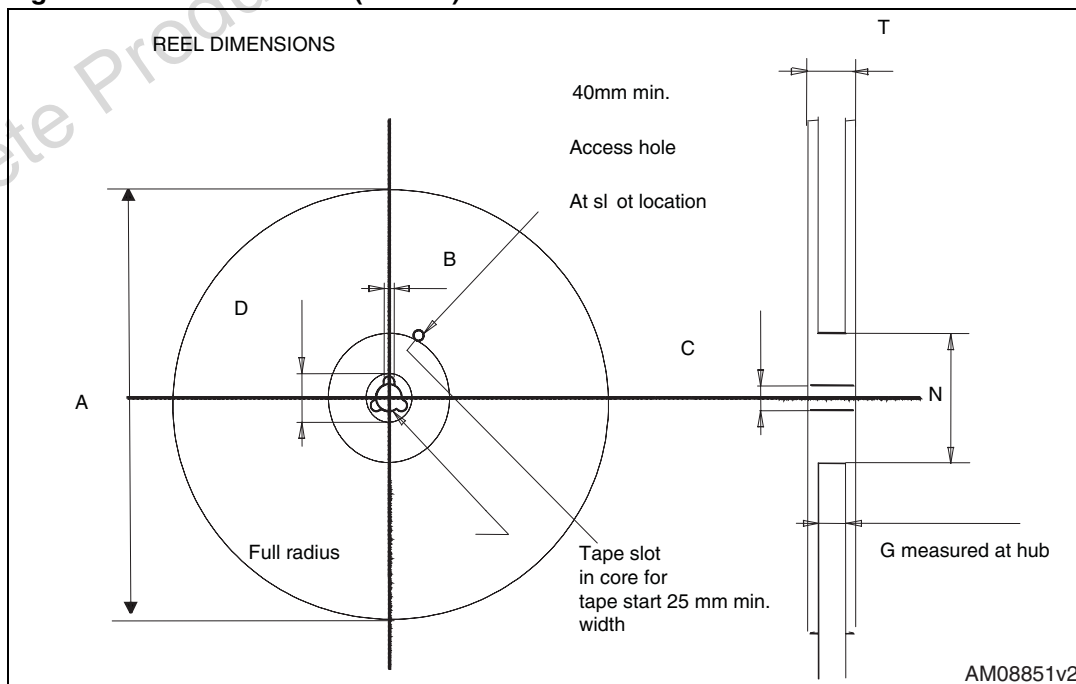
Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 21. Tape for D<sup>2</sup>PAK (TO-263)



AM08852v2

Figure 22. Reel for D<sup>2</sup>PAK (TO-263)



AM08851v2

## 6 Revision history

Table 11. Document revision history

Date	Revision	Changes
11-Jul-2012	1	Initial release.

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